

PMDPB80XP

20 V, dual P-channel Trench MOSFET Rev. 1 — 30 May 2012

Product data sheet

1. **Product profile**

1.1 General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a small and leadless ultra thin DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 1.8 V R_{DSon} rated for low voltage gate drive
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction

1.3 Applications

- Charging switch for portable devices
- DC/DC converters
- Small brushless DC motor drive
- Power management in battery-driven portables
- Hard disc and computing power management

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-	-3.7	Α
Static characte	eristics (per transistor)						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.7 \text{ A}; T_j = 25 \text{ °C}$		-	80	102	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D4 D0
2	G1	gate TR1	6 5 4	D1 D2 _ _
3	D2	drain TR2		
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1	1 2 3	G1 S1 S2 G2
7	D1	drain TR1	Transparent top view	017aaa258
8	D2	drain TR2	SOT1118 (DFN2020-6)	

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMDPB80XP	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1118			

4. Marking

Table 4. Marking codes

Type number	Marking code
PMDPB80XP	1U

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or					
V_{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	<u>[1]</u>	-	-3.7	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	<u>[1]</u>	-	-2.7	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	<u>[1]</u>	-	-1.7	Α
I _{DM}	peak drain current	$T_{amb} = 25 ^{\circ}C$; single pulse; $t_p \le 10 \mu s$		-	-11	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	485	mW
			[1]	-	1100	mW
		T _{sp} = 25 °C		-	6250	mW
Source-drai	n diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-1.1	Α
Per device						
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

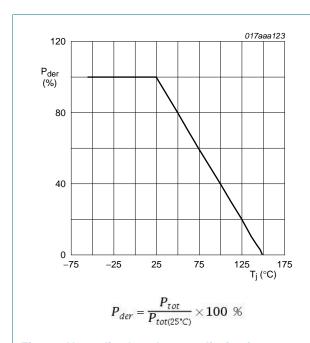
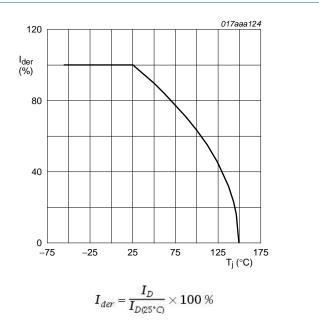


Fig 1. Normalized total power dissipation as a function of junction temperature



ig 2. Normalized continuous drain current as a function of junction temperature

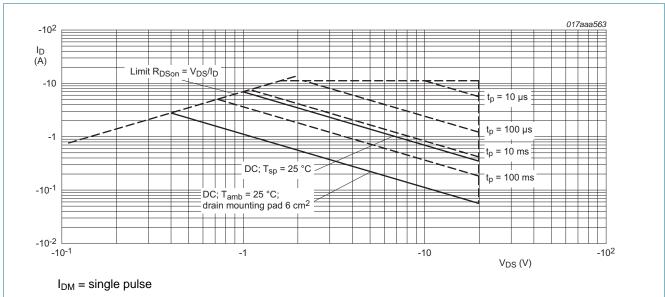


Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	225	260	K/W
			[2]	-	99	115	K/W
		in free air; t ≤ 5 s	<u>[2]</u>	-	54	62	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point	in free air		-	16	20	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

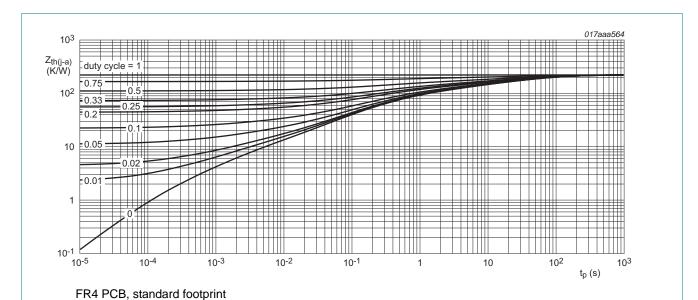


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

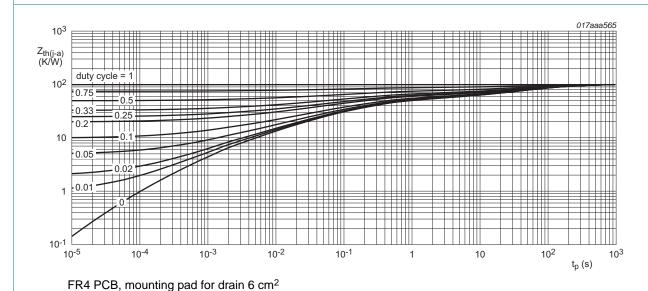


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.4	-0.6	-1	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R _{DSon}	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -2.7 \text{ A}; T_j = 25 \text{ °C}$	-	80	102	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.7 \text{ A}; T_j = 150 \text{ °C}$	-	116	148	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -2.5 \text{ A}; T_j = 25 \text{ °C}$	-	95	125	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -1.1 \text{ A}; T_j = 25 \text{ °C}$	-	120	156	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -2.7 \text{ A}; T_j = 25 \text{ °C}$	-	15	-	S
Dynamic	characteristics (per transist	or)				
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -2.7 A; V_{GS} = -4.5 V;	-	5.7	8.6	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.7	-	nC
Q_{GD}	gate-drain charge		-	0.96	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V;}$	-	550	-	pF
C _{oss}	output capacitance	$T_j = 25 ^{\circ}\text{C}$	-	63	-	pF
C _{rss}	reverse transfer capacitance		-	53	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -2.7 A; V_{GS} = -4.5 V;	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	14	-	ns
t _{d(off)}	turn-off delay time		-	120	-	ns
t _f	fall time		-	50	-	ns
Source-d	rain diode (per transistor)					
V_{SD}	source-drain voltage	$I_S = -1.1 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_i = 25 \text{ °C}$	-	-0.8	-1.2	V

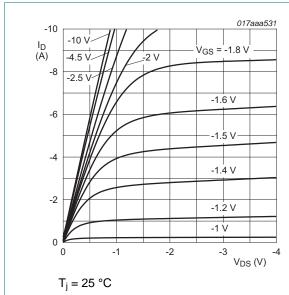


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

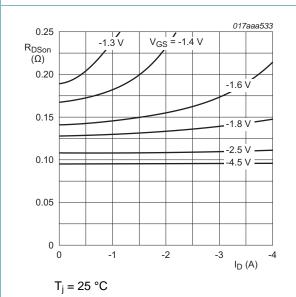


Fig 8. Drain-source on-state resistance as a function of drain current; typical values

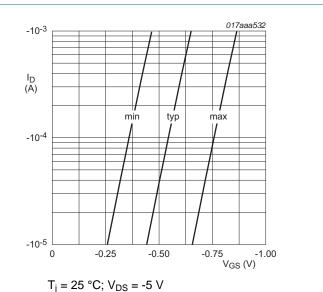


Fig 7. Sub-threshold drain current as a function of gate-source voltage

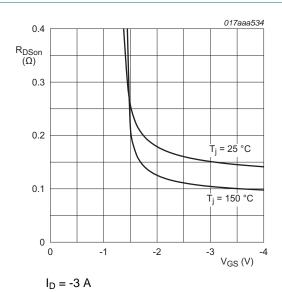


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

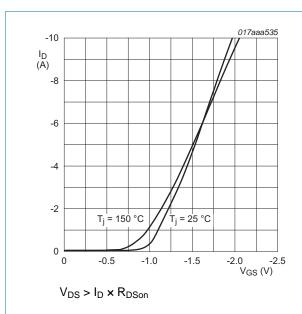


Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

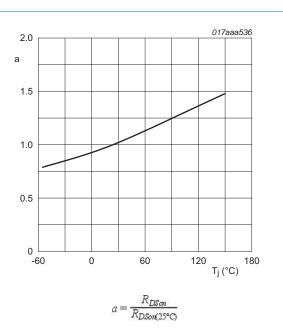


Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

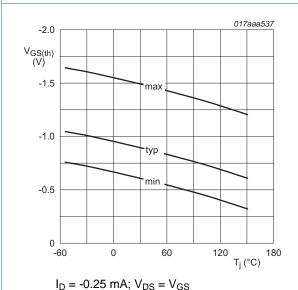
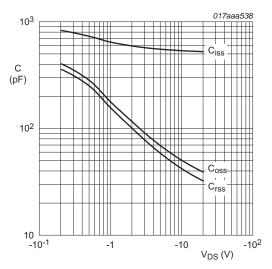
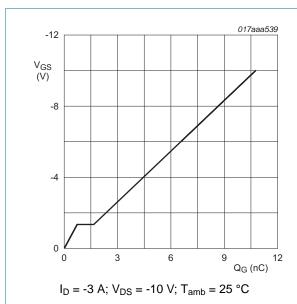


Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



V_{GS}(pl)

V_{GS}(pl)

V_{GS}(th)

V_{GS}

Q_{GS1}

Q_{GS2}

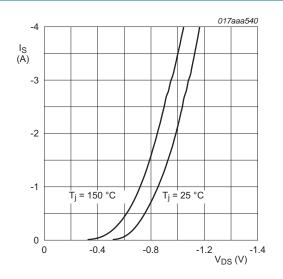
Q_{GS}

Q_G(tot)

017aaa137

Fig 14. Gate-source voltage as a function of gate charge; typical values

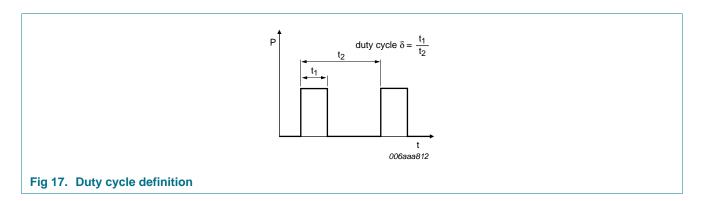
Fig 15. Gate charge waveform definitions



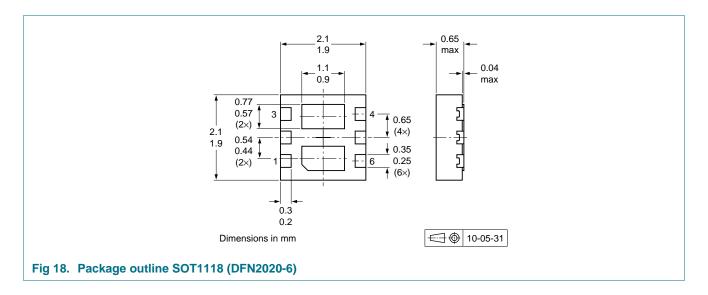
 $V_{GS} = 0 V$

Fig 16. Source current as a function of source-drain voltage; typical values

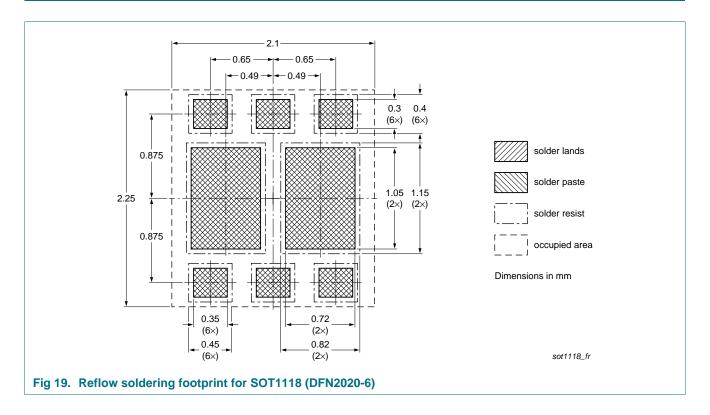
8. Test information



9. Package outline



10. Soldering



Nexperia PMDPB80XP

20 V, dual P-channel Trench MOSFET

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMDPB80XP v.1	20120530	Product data sheet	-	-

12. Legal information

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Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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